

Session Code	[09] WeJ3
Session Title	Semiconductor Materials and Devices for Neuromorphic Devices 3
Date and Time	Wednesday, October 6, 2021 / 15:00-16:00
Session Room	Room J (401)
Session Chair(s)	Sungjae Cho (KAIST, Korea)

[[09] WeJ3-1] **[Online] 15:00-15:15**

Low-Power Synaptic Memtransistors based on Vanadium Oxides

Shahid Iqbal, Le Thai Duy, and Hyungtak Seo (*Ajou Univ., Korea*)

[[09] WeJ3-2] **[Online] 15:15-15:30**

Li Compound-Based Two-Terminal Artificial Synaptic Devices using Atomic Layer Deposition

Hye Rim Kim, Tae Joo Park, Hyun Seung Choi, Su Yong Park (*Hanyang Univ., Korea*), and Gun Hwan Kim (*KRICT, Korea*)

[[09] WeJ3-3] **15:30-15:45**

3-Dimensional Neuromorphic System Consisting of MOSFET and RRAM Crossbar Array Devices for Artificial Hardware Device

Yurim Jeon, Haider Abbas, and Changhwan Choi (*Hanyang Univ., Korea*)

[[09] WeJ3-4] **[Online] 15:45-16:00**

Diffusive Memristors for Neural Network Emulation

Rivu Midya (*Univ. of Massachusetts, USA*), Zhongrui Wang (*The Univ. of Hong Kong, Hong Kong*), Shiva Asapu, Mingyi Rao (*Univ. of Massachusetts, USA*), Wenhao Song, Ye Zhuo (*Univ. of Southern California, USA*), Navnidhi Upadhyay (*Univ. of Notre Dame, USA*), Qiangfei Xia (*Univ. of Massachusetts, USA*), and J Joshua Yang (*Univ. of Southern California, USA*)